#### SiC walls from a core-integration perspective in DIII-D

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#### Presented at the DIII-D Wall Change Community Workshop

June 12-13, 2024





## Figure of Merit: Lowering Z<sub>eff</sub>

- $v_i^* \sim Z_{eff}^4$  and  $v_e^* \sim Z_{eff}$  Sauter PoP 1999
- $Z_{eff} \downarrow \rightarrow$  higher bootstrap current
  - Easier to avoid ballooning limits and access reactor-relevant peeling-limited pedestals
  - Important for Super H-Mode and SVR project
- Less intrinsic impurities allows greater control over Z<sub>eff</sub> with extrinsic (puffed) impurities
  - More control over  $Z_{eff}$  = easier to navigate into Super H-Mode channel







## DIVIMP simulations predict overall decrease in $Z_{\rm eff}$

- Step 1: Constrain graphite wall only case against CER data to instill confidence in transport coefficients
  - Comparing as if C6+ is only impurity since that's what CER assumes



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## DIVIMP simulations predict overall decrease in $Z_{\rm eff}$

#### Step 2: Repeat simulation with SiC walls

- Vary carbon and silicon plasma content to give range of possibilities for sputtering (f\_ = 0.2-2%, f\_{Si} = f\_C / 10)



- DIVIMP simulations show SiC could lower Z<sub>eff</sub> relative to graphite
- Self-conditioning effect
  expected to <u>further lower</u> Z<sub>eff</sub>
  due to oxygen gettering

Next topic

#### SiC walls may be expected to "self-condition"

SiC surface will quickly amorphize

Sizyuk APS 2023



### SiC walls may be expected to "self-condition"

- SiC surface will quickly amorphize
- Sizyuk APS 2023
- Surface composition identical to siliconization with graphite walls
  - Expect similar conditioning benefits, dangerous silane not needed (safer!)



#### **Backup Slides**



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## Silicon carbide traps hydrogen at high temperatures, requiring high surface temperatures to slow accumulation rate

- D is retained in higher temperature traps in SiC (~900 K) than in W (~600 K)
- Increasing surface temperature during exposure yielded 5-6× decrease in D retention
- Si surface enrichment at low impact energies may influence long-term hydrogen buildup





Koller et al., Nucl. Mat. Energy, 2019



Oya et al., J. Nucl. Mat., 2005



## Difference in co-deposition between C and SiC is unclear; high temperatures reduce co-deposit growth rate

- Co-deposition refers to trapping of H/D/T in re-deposited material
  - high T co-deposition in C cited as primary reason for dismissal as FPP-relevant PFM
- Two studies in last 20 years present conflicting results on difference in co-deposition between graphite and SiC
  - role of co-deposit composition is unclear





### Tritium retention is unresolved issue

Hydrogen retention in SiC slightly higher compared to graphite



#### **Mitigation strategies**

- Oxygen baking?
  - Presence of Si in Si/C deposits severely hindered hydrogen removal
  - Likewise for B in B/C deposits

Cruse In Review

Shahid FST 2021

 Operate with hot walls >500-800 °C

# This is the biggest drawback of SiC (and C) as a wall material

High-Z may not fare any better due to large amounts of injected powder...

Stangeby PPCF 2022

Various talks at PSI 2024

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#### SiC walls could simplify blanket designs





staying stop researching it)

#### SiC walls could simplify blanket designs



